

查询"2SA1272"供应 **SILICON PNP TRANSISTOR**
EPITAXIAL PLANAR TYPE (PCT PROCESS)

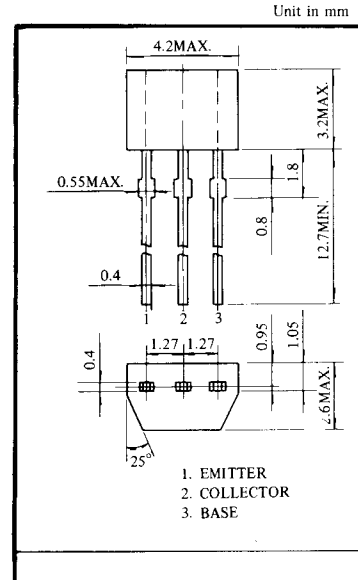
2SA 1272

APPLICATION

- Low Frequency Amplifier Applications.

FEATURES

- High h_{FE} : $h_{FE}=100\sim320$.
- Complementary to 2SC3204.



MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT	CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-35	V	Emitter Current	I_E	800	mA
Collector-Emitter Voltage	V_{CEO}	-30	V	Collector Power Dissipation	P_C	300	mW
Emitter-Base Voltage	V_{EBO}	-5	V	Junction Temperature	T_J	125	°C
Collector Current	I_C	-800	mA	Storage Temperature Range	T_{stg}	-55~125	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = -30V, I_E = 0$	-	-	-100	nA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -5V, I_C = 0$	-	-	-100	nA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -10mA$	-30	-	-	V
Dc Current Gain	$h_{FE(1)NOTE}$	$V_{CE} = -1V, I_C = -100mA$	100	-	320	
	$h_{FE(2)}$	$V_{CE} = -1V, I_C = -700mA$	35	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	$I_C = -500mA, I_B = -20mA$	-	-	-0.7	V
Base-Emitter Voltage	V_{BE}	$V_{CE} = -1V, I_C = -10mA$	-0.5	-	-0.8	V
Transition Frequency	f_T	$V_{CE} = -5V, I_C = -10mA$	-	120	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -10V, f = 1MHz$	-	19	-	pF

NOTE: According to $h_{FE(1)}$ Classified as follows.

0	100~200	Y	160~320
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